

**AMENDMENTS TO THE CLAIMS**

No amendments are made by the present Response. A listing of all claims and their current status in accordance with 37 C.F.R. § 1.121(c) is provided below.

1. (previously presented) A method of configuring a system comprising:  
  
reading operating current values from a non-volatile memory device on a memory module, wherein the memory module comprises a plurality of volatile memory devices, and wherein the operating current values comprise operating currents uniquely corresponding to a lot in which the volatile memory devices were manufactured; and  
  
configuring the system in accordance with the operating current values from the non-volatile memory device on the memory module.
2. (original) The method, as set forth in claim 1, wherein reading comprises reading operating current values from a serial presence detect device.
3. (original) The method, as set forth in claim 1, wherein reading comprises reading operating current values from a non-volatile memory device on a dual inline memory module.
4. (original) The method, as set forth in claim 1, wherein reading comprises reading the operating current values from the non-volatile memory device during a boot of the system.

5. (original) The method, as set forth in claim 1, wherein configuring comprises setting operating current thresholds in the system in accordance with the operating current values.
6. (original) The method, as set forth in claim 5, comprising throttling the memory module if an actual operating current in the memory module exceeds one of the operating current thresholds.
7. (original) A method of configuring a system comprising:  
reading operating current values from a non-volatile memory device on a memory module, wherein the memory module comprises a plurality of volatile memory devices, and wherein the operating current values comprise operating currents uniquely corresponding to each of the plurality of memory devices; and  
configuring the system in accordance with the operating current values from the non-volatile memory device on the memory module.
8. (original) The method, as set forth in claim 7, wherein reading comprises reading operating current values from a serial presence detect device.
9. (original) The method, as set forth in claim 7, wherein reading comprises reading operating current values from a non-volatile memory device on a dual inline memory module.

10. (original) The method, as set forth in claim 7, wherein reading comprises reading the operating current values from the non-volatile memory device during a boot of the system.
11. (original) The method, as set forth in claim 7, wherein configuring comprises setting operating current thresholds in the system in accordance with the operating current values.
12. (original) The method, as set forth in claim 11, comprising throttling the memory module if an actual operating current in the memory module exceeds one of the operating current thresholds.
13. (original) A method of manufacturing a memory module comprising:  
measuring operating current values in each of a plurality of volatile memory devices;  
storing each of the operating current values corresponding to each of the plurality of  
volatile memory devices in a non-volatile memory device; and  
forming a memory module comprising each of the plurality of volatile memory devices  
and the non-volatile memory device.
14. (original) The method, as set forth in claim 13, wherein measuring comprises measuring the operating current values in each of a plurality of dynamic random access memory devices.

15. (original) The method, as set forth in claim 13, wherein storing comprises storing each of the operating current values corresponding to each of the plurality of volatile memory devices in a serial presence detect device.

16. (original) The method as set forth in claim 13, wherein forming comprises forming a dual inline memory module.

17. (original) A method of manufacturing a memory module comprising:  
measuring operating current values in each of a plurality of volatile memory devices,  
wherein the plurality of volatile memory devices correspond to a single  
manufacturing lot;  
calculating average operating current values for the manufacturing lot;  
storing the average operating current values in a non-volatile memory device; and  
forming a memory module comprising each of the plurality of volatile memory devices  
and the non-volatile memory device.

18. (original) The method, as set forth in claim 17, wherein measuring comprises measuring the operating current values in each of a plurality of dynamic random access memory devices.

19. (original) The method, as set forth in claim 17, wherein storing comprises storing the average operating current values in a serial presence detect device.

20. (original) The method as set forth in claim 17, wherein forming comprises forming a dual inline memory module.
21. (original) A memory module comprising:  
a plurality of volatile memory devices; and  
a non-volatile memory device having operating current values uniquely corresponding to  
a lot in which the plurality of volatile memory devices were manufactured stored  
thereon.
22. (original) The memory module, as set forth in claim 21, wherein the memory module  
comprises a dual inline memory module.
23. (original) The memory module, as set forth in claim 21, wherein each of the plurality of  
volatile memory devices comprises a dynamic random access memory device.
24. (original) The memory module, as set forth in claim 21, wherein the non-volatile  
memory device comprises a serial presence detect device.
25. (original) A memory module comprising:  
a plurality of volatile memory devices; and  
a non-volatile memory device having operating current values uniquely corresponding to  
each of the plurality of volatile memory devices stored thereon.

26. (original) The memory module, as set forth in claim 25, wherein the memory module comprises a dual inline memory module.

27. (original) The memory module, as set forth in claim 25, wherein each of the plurality of volatile memory devices comprises a dynamic random access memory device.

28. (original) The memory module, as set forth in claim 25, wherein the non-volatile memory device comprises a serial presence detect device.

29. (original) A computer system comprising:  
a processor; and  
a memory module coupled to the processor and comprising:  
a plurality of volatile memory devices; and  
a non-volatile memory device having operating current values uniquely  
corresponding to each of the plurality of volatile memory devices stored  
thereon.

30. (original) The computer system, as set forth in claim 29, wherein the memory module comprises a dual inline memory module.

31. (original) The computer system, as set forth in claim 29, wherein each of the plurality of volatile memory devices comprises a dynamic random access memory device.

32. (original) The computer system, as set forth in claim 29, wherein the non-volatile memory device comprises a serial presence detect device.